

PNP Transistor KSB708 datasheet

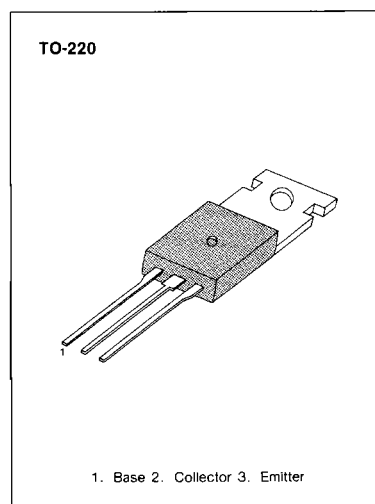
LOW FREQUENCY POWER AMPLIFIER LOW SPEED SWITCHING INDUSTRIAL USE

• Complement to KSD568/569

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage: B707	V_{CEO}	-60	V
: B708	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-7.0	V
Collector Current (DC)	I_C	-7.0	A
* Collector Current (Pulse)	I_C	-15	A
Base Current (DC)	I_B	-3.5	A
Collector Dissipation ($T_a = 25^\circ\text{C}$)	P_C	40	W
Collector Dissipation ($T_c = 25^\circ\text{C}$)	P_C	1.5	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$

* $PW \leq 300\mu\text{s}$, Duty Cycle $\leq 10\%$



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -60\text{V}, I_E = 0$		-10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -5\text{V}, I_C = 0$		-10	μA
* DC Current Gain	h_{FE1}	$V_{CE} = -1\text{V}, I_C = -3\text{A}$	40	200	
	h_{FE2}	$V_{CE} = -1\text{V}, I_C = -5\text{A}$	20		
* Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})$	$I_C = -5\text{A}, I_B = -0.5\text{A}$		-0.5	V
* Base-Emitter Saturation Voltage	$V_{BE}(\text{sat})$	$I_C = -5\text{A}, I_B = -0.5\text{A}$		-1.5	V

* Pulse Test: $PW \leq 350\mu\text{s}$, Duty Cycle $\leq 2\%$

h_{FE} (1) CLASSIFICATION

Classification	R	O	Y
h_{FE} (1)	40-80	60-120	100-200

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